

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S166	358	(pattern\$5 or window) same implant\$5 near10 (carbon or germanium or tin or lead or ge or sn or pb) same (silicon or si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 13:56
S168	2	"20020053316".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 13:59
S171	12	"385574"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 14:00
S170	12	"933801"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 14:00
S169	4	"0933801"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 14:00
S173	4	"6090733".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 14:42
S172	2	"4585299".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 14:42
S167	48	(pattern\$5 or window) near15 implant\$5 near10 (carbon or germanium or tin or lead or ge or sn or pb) same (si or silicon) near10 (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 14:51
S174	3070	(pattern\$5 or window) near15 implant\$5 same (si or silicon) near10 (substrate or wafer) same (si or silicon) near4 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 14:52

S17 5	86	(pattern\$5 or window) near15 implant\$5 near10 (carbon or neutral or argon or ar or germanium or ge or sn or tin or "f" or fluorine) same (si or silicon) near10 (substrate or wafer) same (si or silicon) near4 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 15:25
S17 6	9909	(yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in. or stmicroelectronics. as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 15:28
S17 7	227	S176 and (silicon or si) near5 (substrate or wafer) same implant\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 15:36
S17 9	65	S176 and (silicon or si) near5 (substrate or wafer) same implant\$7 and (pattern\$5 or window) same implant\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 15:37
S17 8	107	S176 and (silicon or si) near5 (substrate or wafer) same implant\$7 and (pattern\$5 or window)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 15:37
S18 0	30	S176 and (silicon or si) near5 (substrate or wafer) same implant\$7 and (pattern\$5 or window) same implant\$5 near10 (neutral\$4 or fluorine or carbon or silicon or germanium or tin or sb or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 15:38
S18 2	14	S176 and (silicon or si) near5 (substrate or wafer) same implant\$7 and (pattern\$5 or window) and implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 15:40
S18 1	5	S176 and (silicon or si) near5 (substrate or wafer) same implant\$7 and (pattern\$5 or window) same implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 15:40
S18 3	20	S176 and (silicon or si) near5 (substrate or wafer) and (pattern\$5 or window) and implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:11

S18 4	1535	(silicon or si) near5 (substrate or wafer) and implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge) same (photo\$1resist or resist or mask\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:14
S18 6	101	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge) same (photo\$1resist or resist or mask\$4) same (si or silicon) near4 deposit\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:19
S18 7	75	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or carbon or tin or sb) same (photo\$1resist or resist or mask\$4) same (si or silicon) near4 deposit\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:20
S18 8	13	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or carbon or tin or sn) same (photo\$1resist or resist or mask\$4) same (si or silicon) near4 deposit\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:21
S18 5	945	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sb or ge) same (photo\$1resist or resist or mask\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:23
S18 9	281	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or carbon or germanium or tin or sn or ge) same (photo\$1resist or resist or mask\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:25
S19 0	285	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or "f") same (pattern\$5 or photo\$1resist or resist or mask\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:29
S19 1	174	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine or "f") same (pattern\$5 or photo\$1resist or resist or mask\$4) not anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:31
S19 2	62	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine) same (pattern\$5 or photo\$1resist or resist or mask\$4) not anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:43

S19 3	115	(silicon or si) near5 (substrate or wafer) same implant\$5 near10 (neutral\$4 or fluorine) same (pattern\$5 or photo\$1resist or resist or mask\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:55
S19 5	2	"5584936".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:59
S19 4	20191	(silicon or si) near5 (substrate or wafer) same implant\$5 same (pattern\$5 or photo\$1resist or resist or mask\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/13 18:59
S19 6	367	(si silicon) near5 epitax\$5 near5 (deposit\$4 or grow\$4) same pattern\$5 near5 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:14
S19 7	170	(si silicon) near5 epitax\$5 near5 (deposit\$4 or grow\$4) near15 pattern\$5 near5 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:15
S20 2	49	(si silicon) near5 (grow\$5 or deposit\$4) near10 epitax\$4 near15 pattern\$5 near5 substrate same implant\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:16
S20 1	552	(si silicon) near5 (grow\$5 or deposit\$4) near15 pattern\$5 near5 substrate same implant\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:16
S20 0	1	(si silicon) near5 (grow\$5 or deposit\$4) near15 pattern\$5 near5 substrate same implant\$5 near5 carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:16
S19 9	1	(si silicon) near5 epitax\$5 near15 pattern\$5 near5 substrate same implant\$5 near5 carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:16
S19 8	1	(si silicon) near5 epitax\$5 near5 (deposit\$4 or grow\$4) near15 pattern\$5 near5 substrate same implant\$5 near5 carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:16

S20 3	19030	implant\$5 same (si or silicon) near5 (substrate or wafer) same (mask\$4 or pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:33
S20 8	1082	ion near3 (silicon or germanium or fluorine or si ge f) near3 implant\$5 near15 (si or silicon) near5 (substrate or wafer) near15 (mask\$4 or pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:34
S20 7	1691	ion near3 (silicon or germanium or fluorine or si ge f) near3 implant\$5 near15 (si or silicon) near5 (substrate or wafer) same (mask\$4 or pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:34
S20 6	2858	ion near3 (silicon or germanium or fluorine or si ge f) near3 implant\$5 same (si or silicon) near5 (substrate or wafer) same (mask\$4 or pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:34
S20 5	4397	(silicon or germanium or fluorine or si ge f) near3 implant\$5 same (si or silicon) near5 (substrate or wafer) same (mask\$4 or pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:34
S20 4	8980	(silicon or germanium or fluorine or si ge f) near10 implant\$5 same (si or silicon) near5 (substrate or wafer) same (mask\$4 or pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:34
S20 9	39	ion near3 (germanium or ge fluorine f) near3 implant\$5 near15 (si or silicon) near5 (substrate or wafer) near15 (mask\$4 or pattern\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:30
S21 1	0	"6191463".pn. and Cvd same temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:41
S21 0	2	"5821158".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:41
S21 7	152	polysilicon near5 (Cvd or chemical near2 vapor near2 deposit\$4) near5 temperature near5 low	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:42

S21 6	7722	polysilicon near5 (Cvd or chemical near2 vapor near2 deposit\$4) near5temperature near5 low	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:42
S21 5	181	polysilicon near5 (Cvd or chemical near2 vapor near2 deposit\$4) near10 temperature near5 low	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:42
S21 4	455	polysilicon near10 (Cvd or chemical near2 vapor near2 deposit\$4) near10 temperature near5 low	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:42
S21 3	857	polysilicon near10 (Cvd or chemical near2 vapor near2 deposit\$4) near10 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:42
S21 2	1	"6191463".pn. and polysilicon same temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:42
S21 9	36	polysilicon near5 (Cvd or chemical near2 vapor near2 deposit\$4) near5 temperature near5 low and @py<"1998"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:43
S21 8	55	polysilicon near5 (Cvd or chemical near2 vapor near2 deposit\$4) near5 temperature near5 low and @py<"2000"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:43
S22 0	7	polysilicon near5 (Cvd or chemical near2 vapor near2 deposit\$4) near5 temperature near5 low same gate and @py<"1998"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 21:20
L1	80	(yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 10:54
L2	47	(yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in. and implant\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 10:55

L5	8	"386574"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 11:00
L4	5	"0386574"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 11:00
L3	29	(yvon near2 gris or germaine near2 troillard or jocelyne near2 mourier).in. and implant\$5 and (silicon or si) near10 single near2 crystal\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 11:00